

# **NPN General Purpose Amplifier**

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1µ to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	100	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		PN2484	*MMBT2484		
PD	Total Device Dissipation	625	350	mW	
	Derate above 25°C	5.0	2.8	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PN2484 / MMBT2484

# NPN General Purpose Amplifier (continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units

## OFF CHARACTERISTICS

BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, \ I_{B} = 0$	60		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10$ mA, $I_{\rm E} = 0$	60		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	6.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 45 \text{ V}, I_E = 0$ $V_{CB} = 45 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		10 10	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	nA

## **ON CHARACTERISTICS**

h <sub>FE</sub>	DC Current Gain	$ \begin{split} I_{C} &= 1.0 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 10 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 100 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 100 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ T_{A} &= -55^{\circ}\text{C} \\ I_{C} &= 500 \; \mu \text{A}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 1.0 \; \text{mA}, \; V_{CE} = 5.0 \; \text{V} \\ I_{C} &= 10 \; \text{mA}, \; V_{CE} = 5.0 \; \text{V} \end{split} $	30 100 175 20 200 250	500 800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{C} = 1.0 \text{ mA}, I_{B} = 0.1 \text{ mA}$		0.35	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 100 \ \mu A, \ V_{CE} = 5.0 \ V$	0.5	0.7	V

# SMALL SIGNAL CHARACTERISTICS

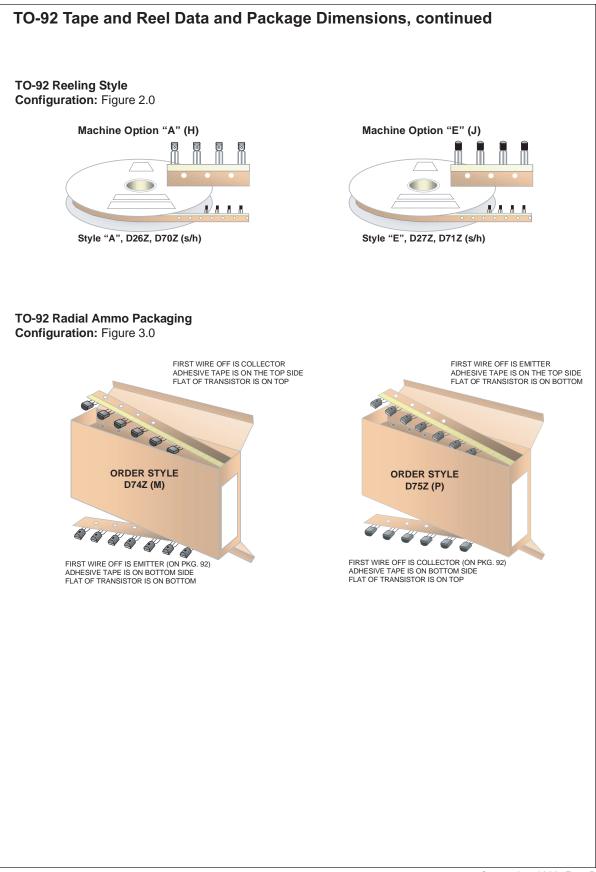
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> =5.0 V, f = 140 kHz	6.	0	pF
Cibo	Input Capacitance	V <sub>EB</sub> = 0.5 V, f = 140 kHz	6.	0	pF
NF	Noise Figure	$    I_{C} = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}, \\ R_{S} = 10 \text{k}, \text{f} = 1.0 \ \text{kHz}, \text{BW} = 200 \ \text{Hz} $	3.	0	dB

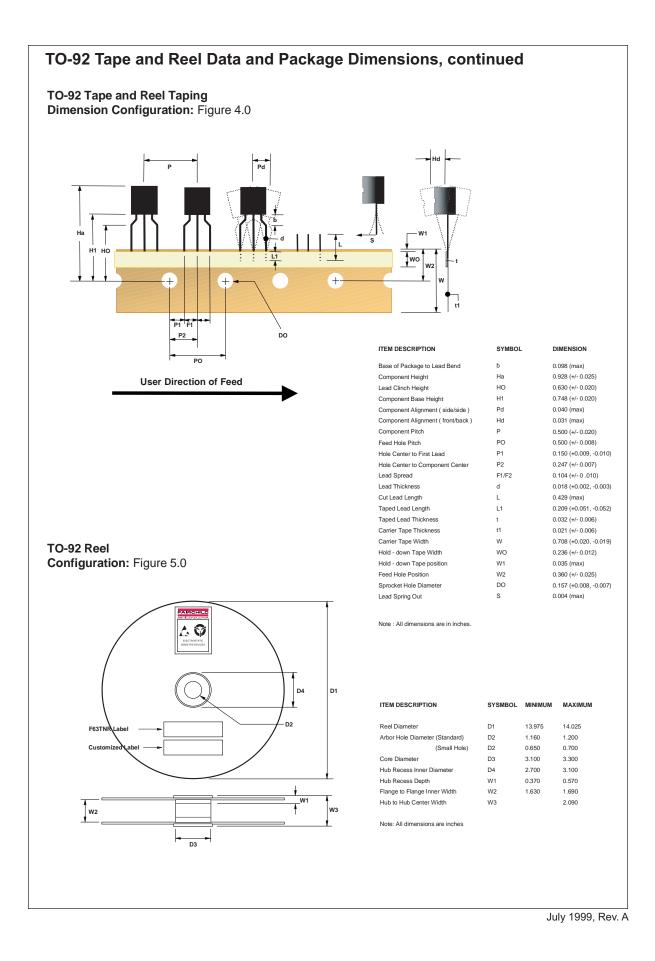
\*Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  3.0%

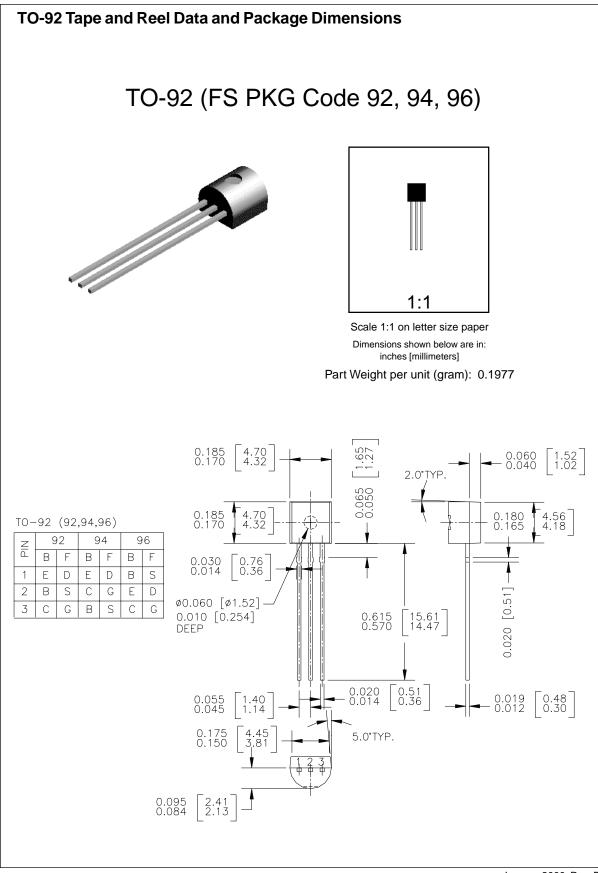


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